



DMP2035UFDF

P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

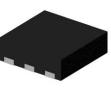
V _{(BR)DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	29mΩ @ V _{GS} = -4.5V	-6.9A
-20V	39mΩ @ V _{GS} = -2.5V	-5.9A

Description and Applications

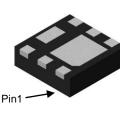
This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- **Battery Management Application**
- **Power Management Functions**
- **DC-DC Converters**









Bottom View

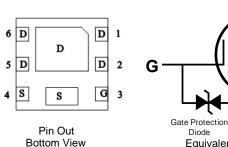
U-DFN2020-6 (Type F)

Features and Benefits

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- Low On-Resistance
- **ESD** Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: U-DFN2020-6 (Type F) •
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @
- Weight: 0.0065 grams (Approximate)



S Equivalent Circuit

D

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2035UFDF-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel
DMP2035UFDF-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



P8 = Product Type Marking Code

YM = Date Code Marking Y = Year (ex: D = 2016)

M = Month (ex: 9 = September)

Date Code Key					-							
Year	2016		2017	2018		2019	2020		2021	2022		2023
Code	D		E	F		G	Н			J		К
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units			
Drain-Source Voltage		V _{DSS}	-20	V		
Gate-Source Voltage		V _{GSS}	±8	V		
Operation on the Desire Oversent (Nate OV) / A EV	Steady State	T _A = +25°C T _A = +70°C	ID	-6.9 -5.5	А	
Continuous Drain Current (Note 6) V_{GS} = -4.5V	t<10s	T _A = +25°C T _A = +70°C	ID	-8.1 -6.5	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	-40	А		
Continuous Source-Drain Diode Current (Note 6)	Is	-2.5	А			
Avalanche Current (Note 7) L = 0.1mH	I _{AS}	-21	А			
Avalanche Energy (Note 7) L = 0.1mH	E _{AS}	23	mJ			

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Power Dissipation (Note 5)	T _A = +25°C	P	0.66	W	
Total Power Dissipation (Note 5)	T _A = +70°C	PD	0.42		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Devi	180	°C/W	
Thermal Resistance, Sunction to Ambient (Note 5)	t<10s	R _{0JA}	135	C/W	
Total Power Dissipation (Note 6)	T _A = +25°C	D-	2.03	W	
Total Fower Dissipation (Note 0)	T _A = +70°C	PD	1.31	vv	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Р	63		
Thermal Resistance, Junction to Amblent (Note 6)	t<10s	$R_{ hetaJA}$	43	°C/W	
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	17.5			
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)	Symbol	141111	тур	WICK	Unit	
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_{D} = -250 \mu A$
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	—	_	-1	μA	$V_{DS} = -16V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	—	_	±10	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						<u> </u>
Gate Threshold Voltage	V _{GS(TH)}	-0.4	_	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
			20	29		V _{GS} = -4.5V, I _D = -6.4A
Static Drain-Source On-Resistance	Р		24	39	mΩ	$V_{GS} = -2.5V, I_D = -4.8A$
	R _{DS(ON)}	_	31	60	11152	$V_{GS} = -1.8V, I_D = -2.5A$
			40	120		V _{GS} = -1.5V, I _D = -1.5A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1.0A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{ISS}	—	1,808	—		
Output Capacitance	C _{OSS}	—	155	—	pF	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	C _{RSS}	—	117	_		1 = 1.00012
Gate Resistance	R _G	—	32	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (V _{GS} = -4.5V)	Q_{G}	—	20.5	_		
Gate-Source Charge	Q _{GS}	—	2.8	—	nC	$V_{DS} = -10V, V_{GS} = -4.5V,$ $I_{D} = -4.0A$
Gate-Drain Charge	Q _{GD}	—	4.1	—		$I_D = -4.0A$
Turn-On Delay Time	t _{D(ON)}	—	9.1	—		
Turn-On Rise Time	t _R	—	12.3	—		$V_{DS} = -10V, V_{GS} = -4.5V,$
Turn-Off Delay Time	t _{D(OFF)}	—	120	_	ns	$R_{G} = 6\Omega, I_{D} = -1.0A$
Turn-Off Fall Time	t _F	—	54	—		
Reverse Recovery Time	t _{RR}	—	23.1	_	ns	I _F = -1.0A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	_	8.3		nC	I _F = -1.0A, di/dt = 100A/µs

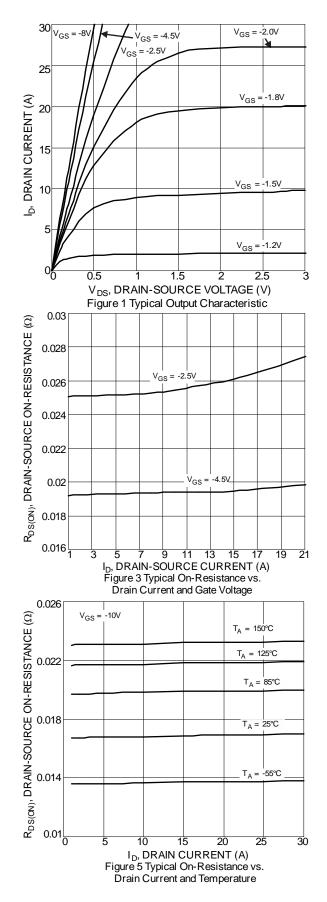
 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate. Notes:

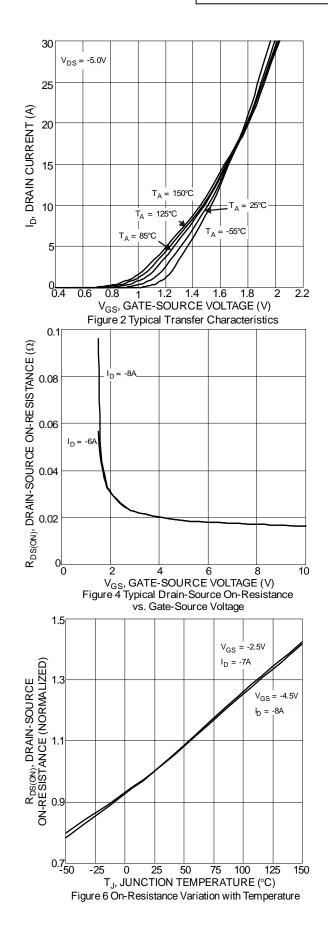
7. IAS and EAS rating are based on low frequency and duty cycles to keep T_J = +25°C.

8. Short duration pulse test used to minimize self-heating effect.

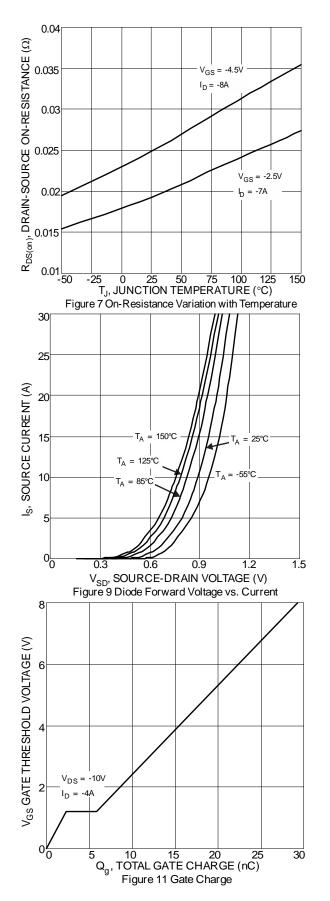
9. Guaranteed by design. Not subject to product testing.

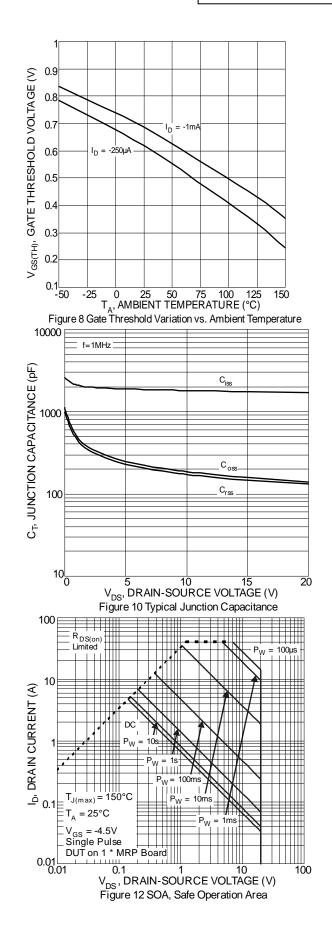




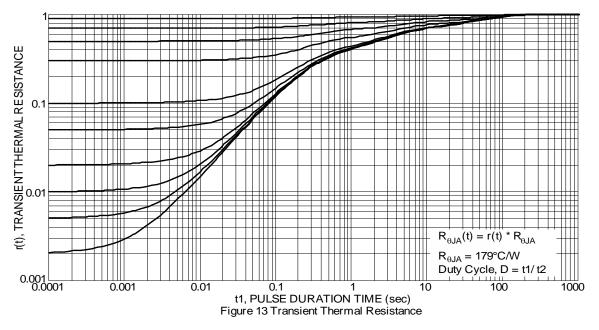








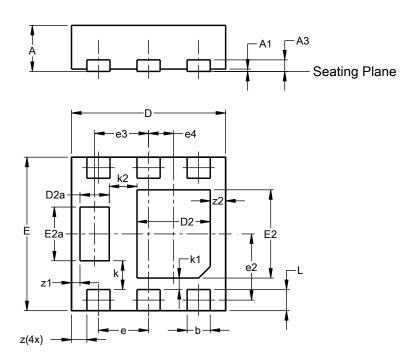






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

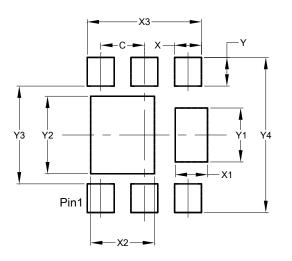


U-DFN2020-6 (Type F)

U-DFN2020-6 (Type F)							
Dim	Min Max Typ						
Α	0.57	0.63	0.60				
A1	0.00	0.05	0.03				
A3	-	-	0.15				
b	0.25	0.35	0.30				
D	1.95	2.05	2.00				
D2	0.85	1.05	0.95				
D2a	0.33	0.33 0.43 0.38					
E	1.95	2.00					
E2	1.05 1.25 1.1						
E2a	0.65 0.75 0.70						
е	0.65 BSC						
e2	0).863 BS	SC				
e3		0.70 BS					
e4).325 BS					
k		0.37 BS					
k1	0.15 BSC						
k2	0.36 BSC						
L	0.225 0.325 0.275						
z		0.20 BS					
z1	0.110 BSC						
z2	0.20 BSC						
	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



U-DFN2020-6 (Type F)

Dimensions	Value			
Dimensions	(in mm)			
С	0.650			
Х	0.400			
X1	0.480			
X2	0.950 1.700 0.425			
X3				
Y				
Y1	0.800			
Y2	1.150			
Y3	1.450			
Y4	2.300			



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